

**IN THE CLAIMS:**

Claims 1-9 (Canceled).

Claim 10 (Original). A method of fabricating a liquid crystal display device, comprising the steps of:

forming an organic insulating film on a substrate;  
forming an alignment film having a first etch rate on the organic insulating film; and  
forming a silicon nitride layer having a second etch rate between the alignment film and the organic insulating film,

wherein the first etch rate is different from the second etch rate.

Claim 11 (Original). The method according to claim 10, further including eliminating the alignment film by dry-etching during rework processing.

Claim 12 (Original). The method according to claim 11, wherein the dry-etching is carried out by using at least one compound gas of SF<sub>6</sub>, O<sub>2</sub>, O<sub>2</sub>+Cl<sub>2</sub>, and CF<sub>4</sub>.

Claim 13 (Original). The method according to claim 12, wherein a ratio of the compound gas is at least about SF<sub>6</sub>:O<sub>2</sub>=1:50.

Claim 14 (Original). The method according to claim 12, wherein a ratio of the compound gas is at least about SF<sub>6</sub>:O<sub>2</sub>=1:70.

Claim 15 (Original). The method according to claim 12, wherein the dry-etching uses a radio frequency power of about 500-1500W.

Claim 16 (Original). The method according to claim 10, wherein the silicon nitride layer includes hydrogen.

Claim 17 (Original). The method according to claim 10, further including the steps of:

- forming a gate line and a gate electrode on the substrate;
- forming a gate insulating film on the gate line, the gate electrode and the substrate;
- forming a semiconductor layer on the gate insulating film; and
- forming a data line, a source electrode and a drain electrode on the gate insulating film.

Claim 18 (Original). The method according to claim 17, further including the step of forming a pixel electrode on the silicon nitride layer to overlap at least one of the data line and the gate line.

Claims 19-27 (Canceled).